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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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# Phase Control Thyristor

## ISOPLUS220™

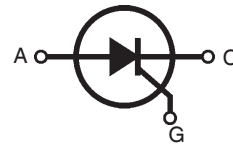
### Electrically Isolated Back Surface

$$V_{RRM} = 800 - 1200 \text{ V}$$

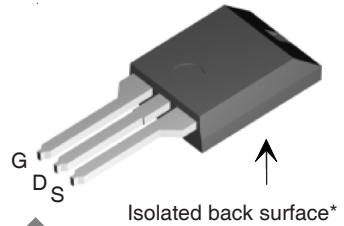
$$I_{T(RMS)} = 35 \text{ A}$$

$$I_{T(AV)M} = 13 \text{ A}$$

$V_{RSM}$ $V_{DSM}$ V	$V_{RRM}$ $V_{DRM}$ V	Type
800	800	CS 19-08ho1C
1200	1200	CS 19-12ho1C



ISOPLUS 220™



Symbol	Test Conditions	Maximum Ratings	
$I_{T(RMS)}$	$T_{VJ} = T_{VJM}$	35	A
$I_{T(AV)M}$	$T_C = 85^\circ\text{C}; 180^\circ \text{ sine}$	13	A
$I_{TSM}$	$T_{VJ} = 45^\circ\text{C}; V_R = 0 \text{ V}$	$t = 10 \text{ ms (50 Hz), sine}$	100 A
		$t = 8.3 \text{ ms (60 Hz), sine}$	105 A
	$T_{VJ} = T_{VJM}; V_R = 0 \text{ V}$	$t = 10 \text{ ms (50 Hz), sine}$	85 A
		$t = 8.3 \text{ ms (60 Hz), sine}$	90 A
$I^2t$	$T_{VJ} = 45^\circ\text{C}; V_R = 0 \text{ V}$	$t = 10 \text{ ms (50 Hz), sine}$	50 $\text{A}^2\text{s}$
		$t = 8.3 \text{ ms (60 Hz), sine}$	45 $\text{A}^2\text{s}$
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ repetitive, $I_T = 20 \text{ A}$ $f = 50 \text{ Hz}, t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$		100 $\text{A}/\mu\text{s}$
	$I_G = 0.08 \text{ A}$ non repetitive, $I_T = I_{T(AV)M}$ $di_G/dt = 0.08 \text{ A}/\mu\text{s}$		500 $\text{A}/\mu\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}; V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$ ; method 1 (linear voltage rise)		500 $\text{V}/\mu\text{s}$
$P_{GM}$	$T_{VJ} = T_{VJM}; t_p = 30 \mu\text{s}$		5 W
$P_{GAV}$	$I_T = I_{T(AV)M}; t_p = 300 \mu\text{s}$		2.5 W
			0.5 W
$V_{RGM}$		10	V
$T_{VJ}$		-40...+125	$^\circ\text{C}$
$T_{VJM}$		125	$^\circ\text{C}$
$T_{stg}$		-40...+125	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz RMS; $I_{ISOL} \leq 1 \text{ mA}$	2500	V~
$T_L$	1.6mm from case; 10s	260	$^\circ\text{C}$
$F_C$	Mounting force	11...65 / 2.4...11	N / lb
Weight		2	g

#### Features

#### Features

- Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- 2500V electrical isolation
- Low cathode-to-tab capacitance (15pF typical)
- Planar passivated chips
- Epoxy meets UL 94V-0
- High performance glass passivated chip
- Long-term stability of leakage current and blocking voltage

#### Applications

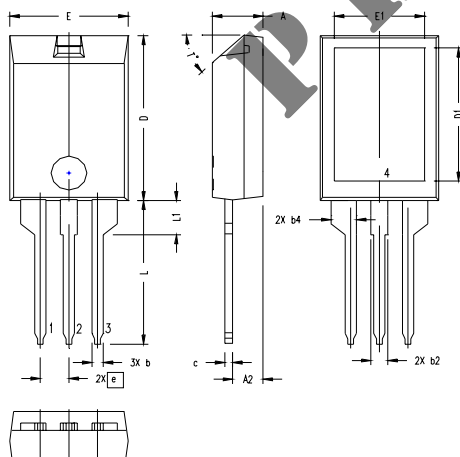
- Motor control
- Power converter
- AC power controller
- Light and temperature control
- SCR for inrush current limiting in power supplies or AC drive

#### Advantages

- Space and weight savings
- Simple mounting

Symbol	Test Conditions	Characteristic Values
$I_{R^1}, I_D$	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	$\leq 1$ mA
$V_T$	$I_T = 30$ A; $T_{VJ} = 25^\circ\text{C}$	$\leq 1.65$ V
$V_{T0}$	For power-loss calculations only ( $T_{VJ} = 125^\circ\text{C}$ )	0.87 V
$r_T$		29 m $\Omega$
$V_{GT}$	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	$\leq 1.5$ V $\leq 2.5$ V
$I_{GT}$	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	$\leq 25$ mA $\leq 50$ mA
$V_{GD}$	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	$\leq 0.2$ V
$I_{GD}$		$\leq 3$ mA
$I_L$	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.08$ A; $di_G/dt = 0.08$ A/ $\mu\text{s}$	$\leq 75$ mA
$I_H$	$T_{VJ} = 25^\circ\text{C}; V_D = 6$ V; $R_{GK} = \infty$	$\leq 50$ mA
$t_{gd}$	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.08$ A; $di_G/dt = 0.08$ A/ $\mu\text{s}$	$\leq 2$ $\mu\text{s}$
$R_{thJC}$	DC current	1.7 K/W
$R_{thCK}$	DC current	typical 0.6 K/W
$a$	Max. acceleration, 50 Hz	50 m/s <sup>2</sup>

## ISOPLUS220 OUTLINE



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.157	.197	4.00	5.00
A2	.098	.118	2.50	3.00
b	.035	.051	0.90	1.30
b2	.049	.065	1.25	1.65
b4	.093	.100	2.35	2.55
c	.028	.039	0.70	1.00
D	.591	.630	15.00	16.00
D1	.472	.512	12.00	13.00
E	.394	.433	10.00	11.00
E1	.295	.335	7.50	8.50
e	.100 BASIC		2.55 BASIC	
L	.512	.571	13.00	14.50
L1	.118	.138	3.00	3.50
T*			42.5°	47.5°

**NOTE:**

1. Bottom heatsink (Pin 4) is electrically isolated from Pin 1, 2, or 3.
2. This drawing will meet dimensional requirement of JEDEC SS Product Outline TO-273 except D and D1 dimension.